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# HM62W8511HC Series

4M High Speed SRAM (512-kword × 8-bit)

# HITACHI

ADE-203-1201 (Z)  
Preliminary  
Rev. 0.0  
Sep. 20, 2000

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## Description

The HM62W8511HC is a 4-Mbit high speed static RAM organized 512-kword × 8-bit. It has realized high speed access time by employing CMOS process (6-transistor memory cell) and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. The HM62W8511HC is packaged in 400-mil 36-pin SOJ for high density surface mounting.

## Features

- Single supply : 3.3 V ± 0.3 V
- Access time : 10 ns (max)
- Completely static memory
  - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
  - All inputs and outputs
- Operating current : 115 mA (max)
- TTL standby current : 40 mA (max)
- CMOS standby current : 5 mA (max)
  - : 1 mA (max) (L-version)
- Data retention current : 0.6 mA (max) (L-version)
- Data retention voltage : 2 V (min) (L-version)
- Center  $V_{CC}$  and  $V_{SS}$  type pinout

Preliminary: The specification of this device are subject to change without notice. Please contact your nearest Hitachi's Sales Dept. regarding specification.

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## **HM62W8511HC Series**

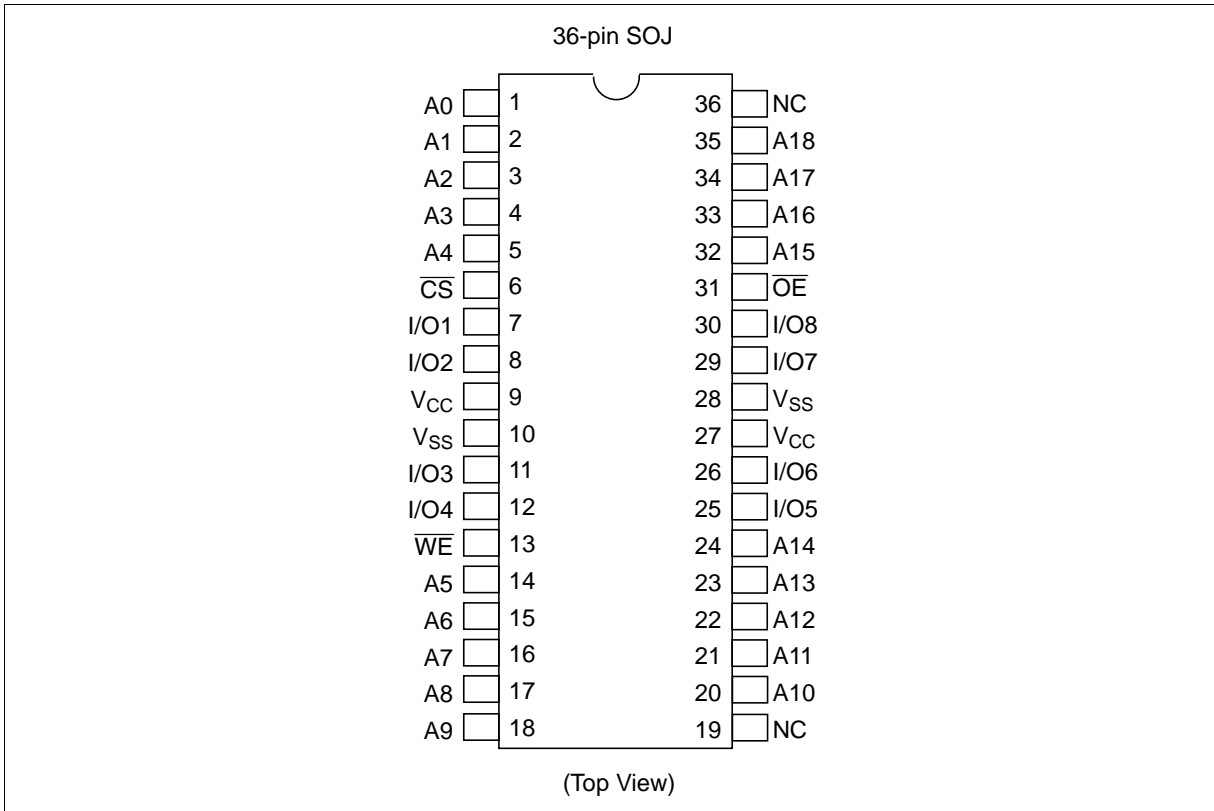
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### **Ordering Information**

<b>Type No.</b>	<b>Access time</b>	<b>Package</b>
HM62W8511HCJP-10	10 ns	400-mil 36-pin plastic SOJ (CP-36D)
HM62W8511HCLJP-10	10 ns	

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Pin Arrangement

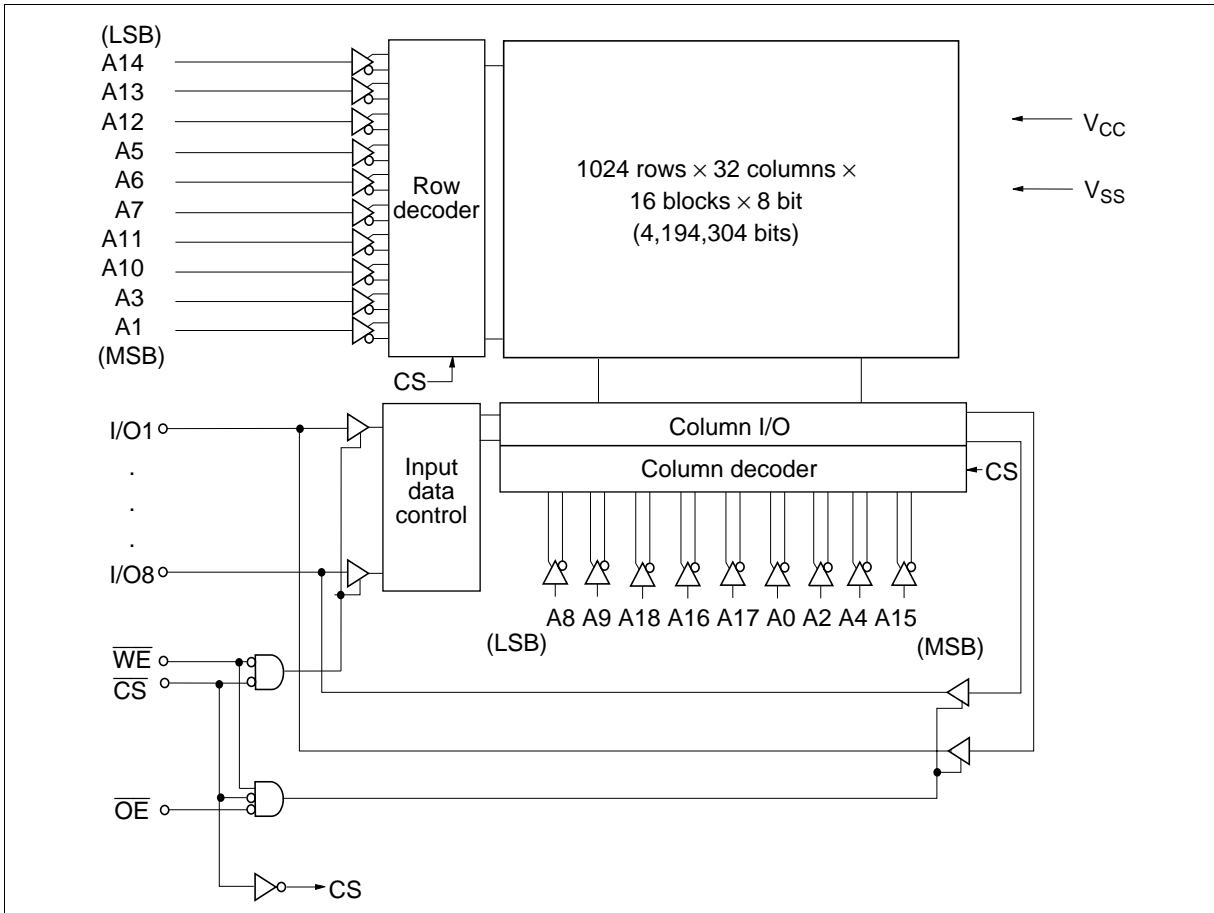


Pin Description

Pin name	Function
A0 to A18	Address input
I/O1 to I/O8	Data input/output
$\overline{CS}$	Chip select
$\overline{OE}$	Output enable
$\overline{WE}$	Write enable
V <sub>CC</sub>	Power supply
V <sub>SS</sub>	Ground
NC	No connection

# HM62W8511HC Series

## Block Diagram



## HM62W8511HC Series

### Operation Table

$\overline{\text{CS}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	Mode	$V_{\text{CC}}$ current	I/O	Ref. cycle
H	×	×	Standby	$I_{\text{SB}}, I_{\text{SB1}}$	High-Z	—
L	H	H	Output disable	$I_{\text{CC}}$	High-Z	—
L	L	H	Read	$I_{\text{CC}}$	Dout	Read cycle (1) to (3)
L	H	L	Write	$I_{\text{CC}}$	Din	Write cycle (1)
L	L	L	Write	$I_{\text{CC}}$	Din	Write cycle (2)

Note: ×: H or L

### Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to $V_{\text{SS}}$	$V_{\text{CC}}$	−0.5 to +4.6	V
Voltage on any pin relative to $V_{\text{SS}}$	$V_{\text{T}}$	−0.5*1 to $V_{\text{CC}}+0.5^{*2}$	V
Power dissipation	$P_{\text{T}}$	1.0	W
Operating temperature	$T_{\text{opr}}$	0 to +70	°C
Storage temperature	$T_{\text{stg}}$	−55 to +125	°C
Storage temperature under bias	$T_{\text{bias}}$	−10 to +85	°C

Notes: 1.  $V_{\text{T}}$  (min) = −2.0 V for pulse width (under shoot) ≤ 6 ns.  
 2.  $V_{\text{T}}$  (max) =  $V_{\text{CC}}+2.0$  V for pulse width (over shoot) ≤ 6 ns.

### Recommended DC Operating Conditions ( $T_{\text{a}} = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	$V_{\text{CC}}^{*3}$	3.0	3.3	3.6	V
	$V_{\text{SS}}^{*4}$	0	0	0	V
Input voltage	$V_{\text{IH}}$	2.0	—	$V_{\text{CC}} + 0.5^{*2}$	V
	$V_{\text{IL}}$	−0.5*1	—	0.8	V

Notes: 1.  $V_{\text{IL}}$  (min) = −2.0 V for pulse width (under shoot) ≤ 6 ns.  
 2.  $V_{\text{IH}}$  (max) =  $V_{\text{CC}}+2.0$  V for pulse width (over shoot) ≤ 6 ns.  
 3. The supply voltage with all  $V_{\text{CC}}$  pins must be on the same level.  
 4. The supply voltage with all  $V_{\text{SS}}$  pins must be on the same level.

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**DC Characteristics** ( $T_a = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$ ,  $V_{SS} = 0\text{V}$ )

Parameter	Symbol	Min	Typ* <sup>1</sup>	Max	Unit	Test conditions
Input leakage current	$ I_{LI} $	—	—	2	$\mu\text{A}$	$V_{in} = V_{SS}$ to $V_{CC}$
Output leakage current	$ I_{LO} $	—	—	2	$\mu\text{A}$	$V_{in} = V_{SS}$ to $V_{CC}$
Operation power supply current	$I_{CC}$	—	—	115	mA	Min cycle $\overline{CS} = V_{IL}$ , $I_{out} = 0\text{ mA}$ Other inputs = $V_{IH}/V_{IL}$
Standby power supply current	$I_{SB}$	—	—	40	mA	Min cycle $\overline{CS} = V_{IH}$ , Other inputs = $V_{IH}/V_{IL}$
	$I_{SB1}$	—	TBD	5	mA	$f = 0\text{ MHz}$ $V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2\text{ V}$ , (1) $0\text{ V} \leq V_{in} \leq 0.2\text{ V}$ or (2) $V_{CC} \geq V_{in} \geq V_{CC} - 0.2\text{ V}$
		—* <sup>2</sup>	TBD* <sup>2</sup>	1.0* <sup>2</sup>		
Output voltage	$V_{OL}$	—	—	0.4	V	$I_{OL} = 8\text{ mA}$
	$V_{OH}$	2.4	—	—	V	$I_{OH} = -4\text{ mA}$

Notes: 1. Typical values are at  $V_{CC} = 3.3\text{ V}$ ,  $T_a = +25^\circ\text{C}$  and not guaranteed.

2. This characteristics is guaranteed only for L-version.

**Capacitance** ( $T_a = +25^\circ\text{C}$ ,  $f = 1.0\text{ MHz}$ )

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input capacitance* <sup>1</sup>	$C_{in}$	—	—	6	pF	$V_{in} = 0\text{ V}$
Input/output capacitance* <sup>1</sup>	$C_{I/O}$	—	—	8	pF	$V_{I/O} = 0\text{ V}$

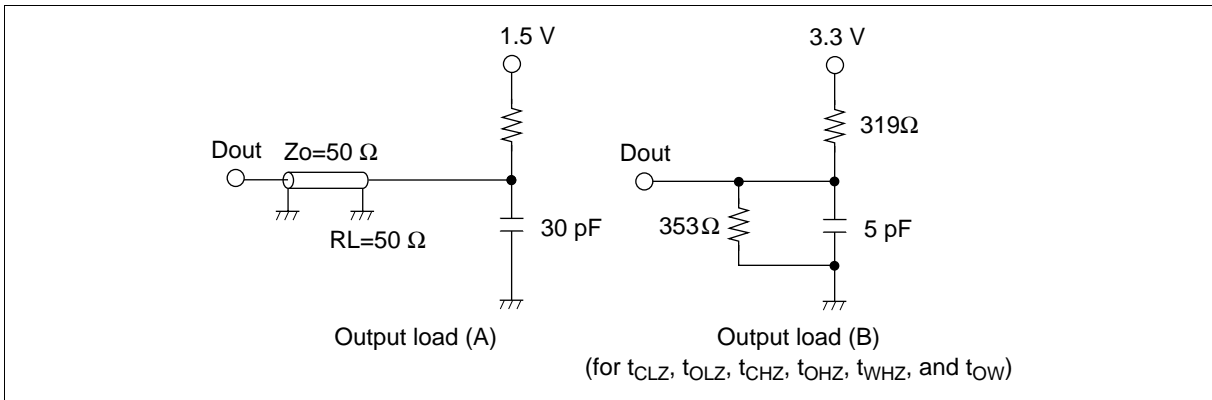
Note: 1. This parameter is sampled and not 100% tested.

## HM62W8511HC Series

**AC Characteristics** ( $T_a = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$ , unless otherwise noted.)

### Test Conditions

- Input pulse levels: 3.0 V/0.0 V
- Input rise and fall time: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures (Including scope and jig)



### Read Cycle

Parameter	Symbol	HM62W8511HC		Unit	Notes
		-10			
		Min	Max		
Read cycle time	$t_{RC}$	10	—	ns	
Address access time	$t_{AA}$	—	10	ns	
Chip select access time	$t_{ACS}$	—	10	ns	
Output enable to output valid	$t_{OE}$	—	5	ns	
Output hold from address change	$t_{OH}$	3	—	ns	
Chip select to output in low-Z	$t_{CLZ}$	3	—	ns	1
Output enable to output in low-Z	$t_{OLZ}$	0	—	ns	1
Chip deselect to output in high-Z	$t_{CHZ}$	—	5	ns	1
Output disable to output in high-Z	$t_{OHZ}$	—	5	ns	1

## HM62W8511HC Series

### Write Cycle

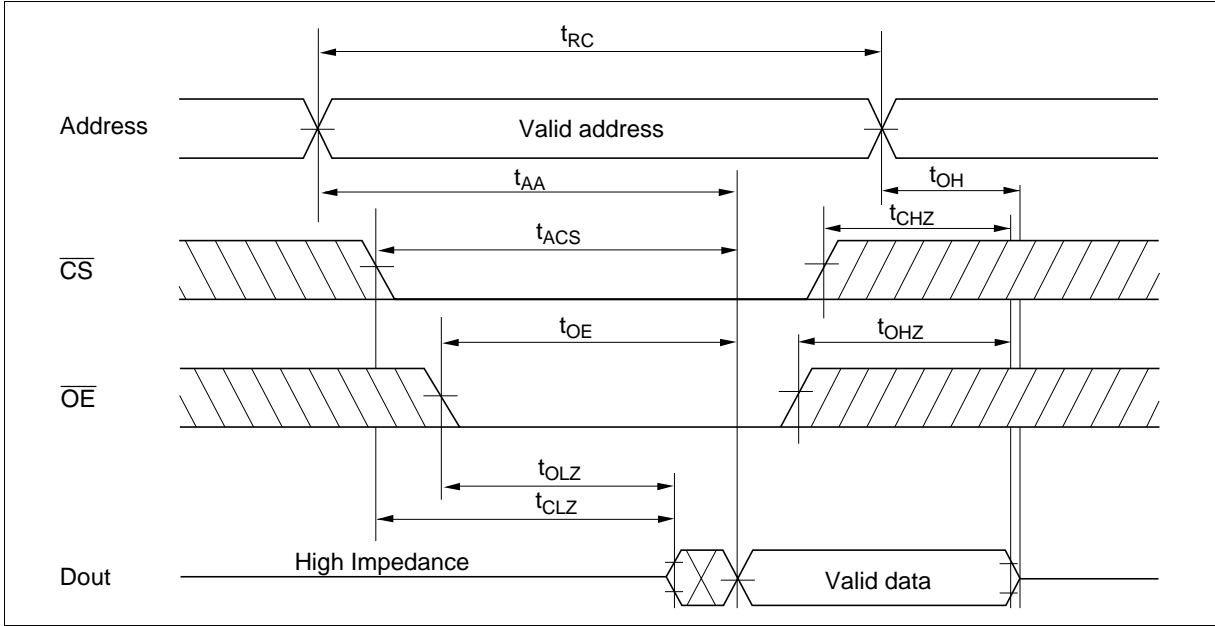
Parameter	Symbol	HM62W8511HC		Unit	Notes
		-10			
		Min	Max		
Write cycle time	$t_{WC}$	10	—	ns	
Address valid to end of write	$t_{AW}$	7	—	ns	
Chip select to end of write	$t_{CW}$	7	—	ns	9
Write pulse width	$t_{WP}$	7	—	ns	8
Address setup time	$t_{AS}$	0	—	ns	6
Write recovery time	$t_{WR}$	0	—	ns	7
Data to write time overlap	$t_{DW}$	5	—	ns	
Data hold from write time	$t_{DH}$	0	—	ns	
Write disable to output in low-Z	$t_{OW}$	3	—	ns	1
Output disable to output in high-Z	$t_{OHZ}$	—	5	ns	1
Write enable to output in high-Z	$t_{WHZ}$	—	5	ns	1

- Note:
1. Transition is measured  $\pm 200$  mV from steady voltage with Load (B). This parameter is sampled and not 100% tested.
  2. Address should be valid prior to or coincident with  $\overline{CS}$  transition low.
  3.  $\overline{WE}$  and/or  $\overline{CS}$  must be high during address transition time.
  4. If  $\overline{CS}$  and  $\overline{OE}$  are low during this period, I/O pins are in the output state. Then, the data input signals of opposite phase to the outputs must not be applied to them.
  5. If the  $\overline{CS}$  low transition occurs simultaneously with the  $\overline{WE}$  low transition or after the  $\overline{WE}$  transition, output remains a high impedance state.
  6.  $t_{AS}$  is measured from the latest address transition to the later of  $\overline{CS}$  or  $\overline{WE}$  going low.
  7.  $t_{WR}$  is measured from the earlier of  $\overline{CS}$  or  $\overline{WE}$  going high to the first address transition.
  8. A write occurs during the overlap of a low  $\overline{CS}$  and a low  $\overline{WE}$ . A write begins at the latest transition among  $\overline{CS}$  going low and  $\overline{WE}$  going low. A write ends at the earliest transition among  $\overline{CS}$  going high and  $\overline{WE}$  going high.  $t_{WP}$  is measured from the beginning of write to the end of write.
  9.  $t_{CW}$  is measured from the later of  $\overline{CS}$  going low to the the end of write.

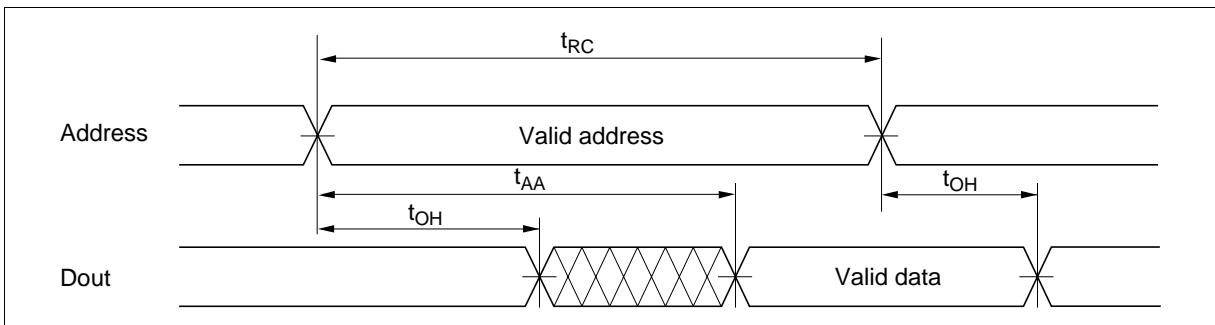


Timing Waveforms

Read Timing Waveform (1) ( $\overline{WE} = V_{IH}$ )

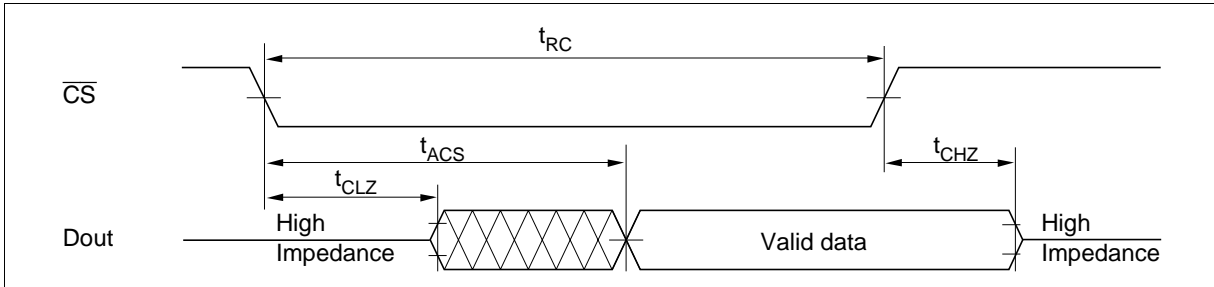


Read Timing Waveform (2) ( $\overline{WE} = V_{IH}, \overline{CS} = V_{IL}, \overline{OE} = V_{IL}$ )

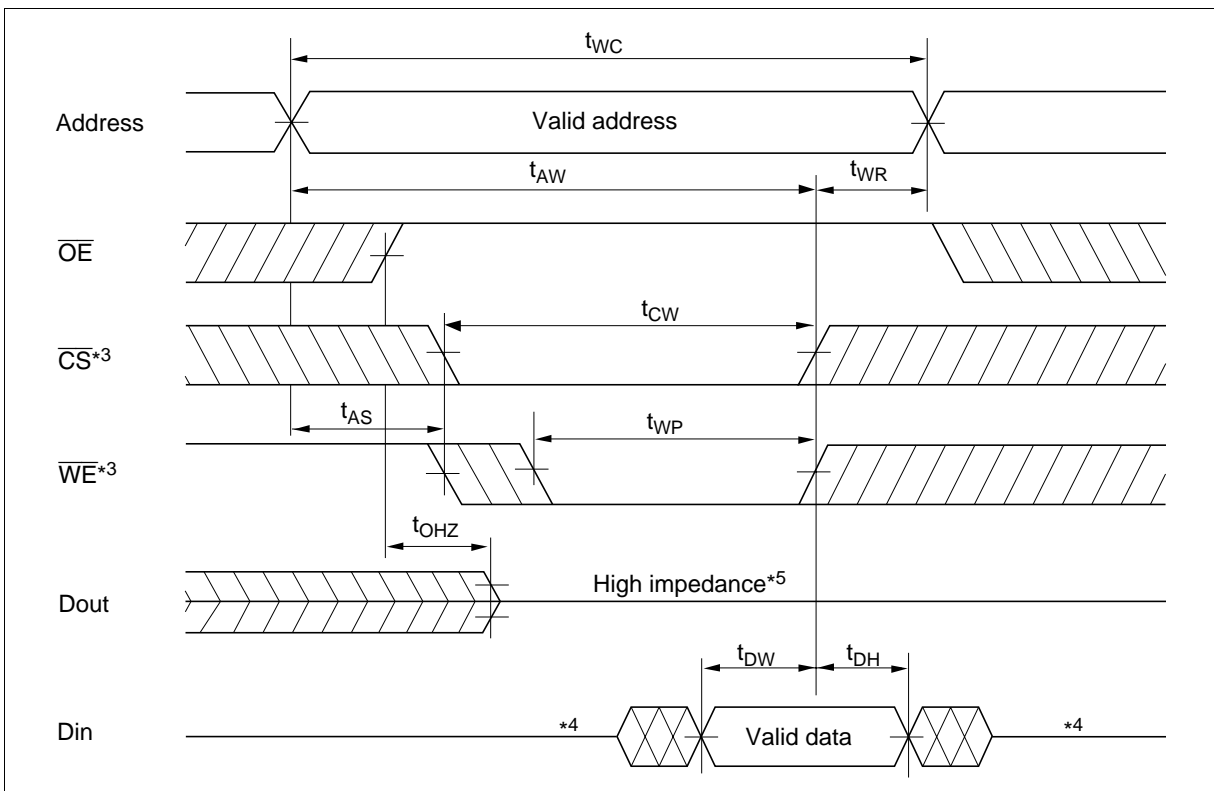


## HM62W8511HC Series

Read Timing Waveform (3) ( $\overline{WE} = V_{IH}$ ,  $\overline{CS} = V_{IL}$ ,  $\overline{OE} = V_{IL}$ )\*<sup>2</sup>

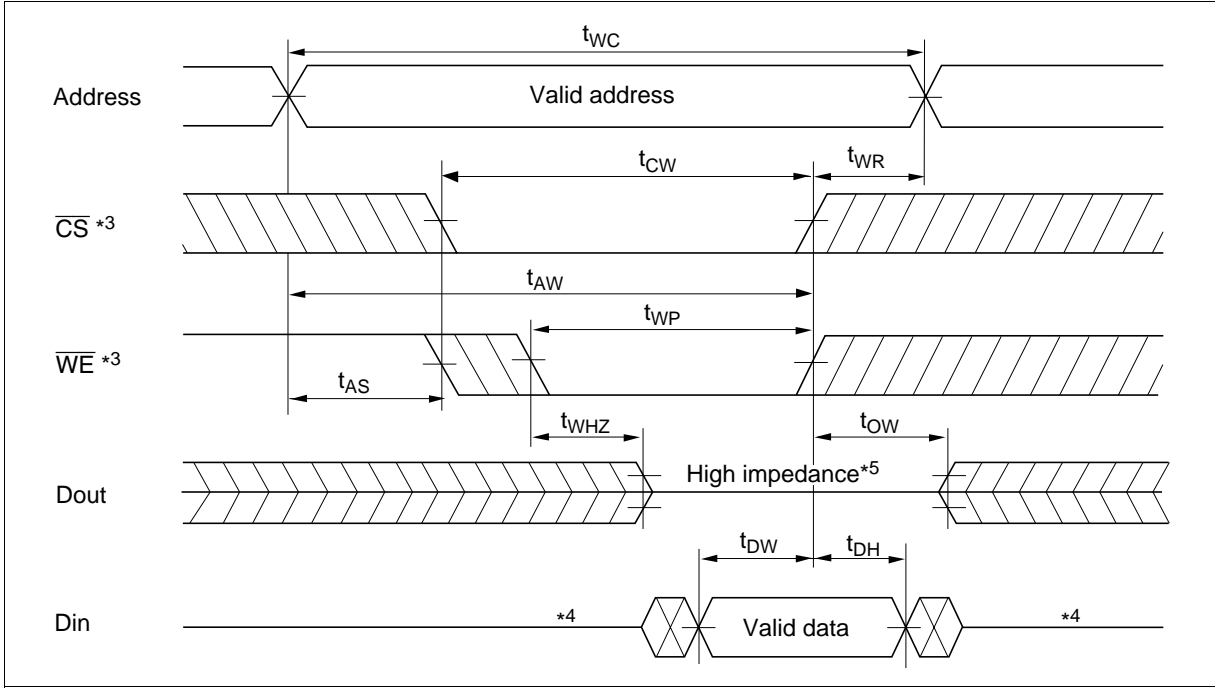


Write Timing Waveform (1) ( $\overline{WE}$  Controlled)



**HM62W8511HC Series**

**Write Timing Waveform (2) ( $\overline{CS}$  Controlled)**



## HM62W8511HC Series

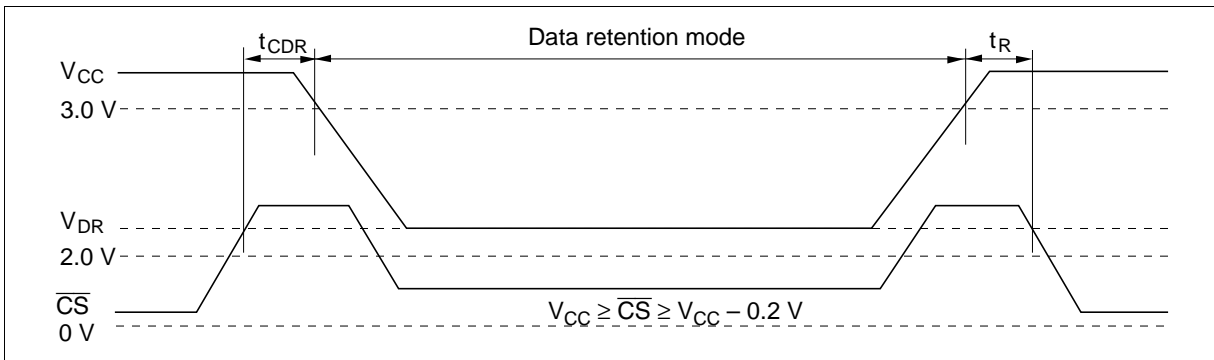
### Low $V_{CC}$ Data Retention Characteristics ( $T_a = 0$ to $+70^\circ\text{C}$ )

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ*1	Max	Unit	Test conditions
$V_{CC}$ for data retention	$V_{DR}$	2.0	—	—	V	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2$ V (1) $0 \text{ V} \leq V_{in} \leq 0.2 \text{ V}$ or (2) $V_{CC} \geq V_{in} \geq V_{CC} - 0.2 \text{ V}$
Data retention current	$I_{CCDR}$	—	TBD	600	$\mu\text{A}$	$V_{CC} = 3 \text{ V}$ , $V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2 \text{ V}$ (1) $0 \text{ V} \leq V_{in} \leq 0.2 \text{ V}$ or (2) $V_{CC} \geq V_{in} \geq V_{CC} - 0.2 \text{ V}$
Chip deselect to data retention time	$t_{CDR}$	0	—	—	ns	See retention waveform
Operation recovery time	$t_R$	5	—	—	ms	

Note: 1. Typical values are at  $V_{CC} = 3.0 \text{ V}$ ,  $T_a = +25^\circ\text{C}$ , and not guaranteed.

### Low $V_{CC}$ Data Retention Timing Waveform

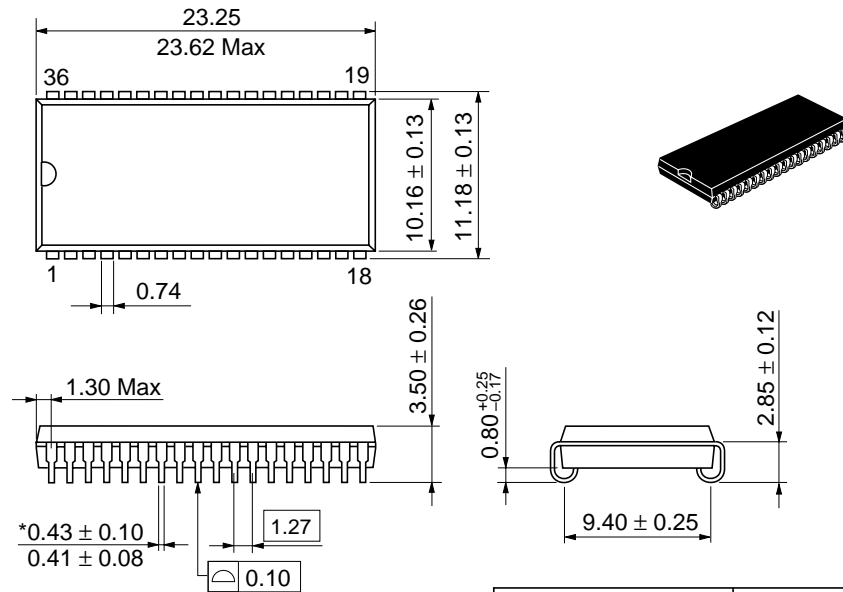


# HM62W8511HC Series

## Package Dimensions

### HM62W8511HCJP/HCLJP Series (CP-36D)

Unit: mm



\*Dimension including the plating thickness  
Base material dimension

Hitachi Code	CP-36D
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.4 g

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## HM62W8511HC Series

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